



# BUK961R6-40E

## N-channel TrenchMOS logic level FET

Rev. 2 — 16 May 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{gst(th)}$  rating of greater than 0.5V at 175 °C

### 1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

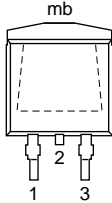
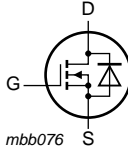
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$V_{GS} = 5\text{ V}; T_{mb} = 25\text{ °C};$ see <a href="#">Figure 1</a>	[1]	-	120	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	357	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see <a href="#">Figure 11</a>	-	1.35	1.6	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; V_{DS} = 32\text{ V};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	40.9	-	nC

[1] Continuous current is limited by package.



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT404 (D2PAK)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BUK961R6-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Marking

**Table 4. Marking codes**

Type number	Marking code
BUK961R6-40E	BUK961R6-40E

## 5. Limiting values

**Table 5. Limiting values**

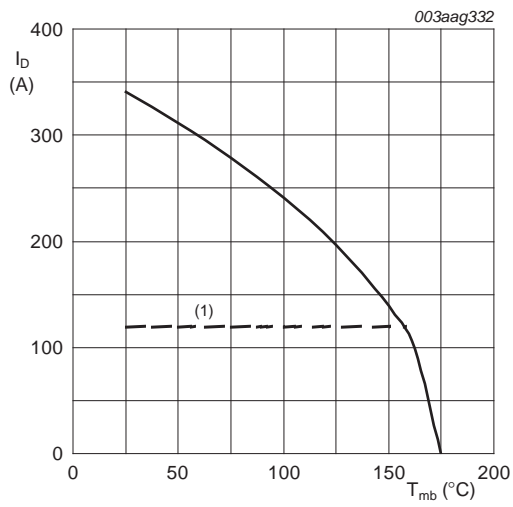
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	40	V	
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	40	V	
$V_{GS}$	gate-source voltage	DC	-10	10	V	
		Pulsed	-15	15	V	
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 5\text{ V};$ see <a href="#">Figure 1</a>	[1]	-	120	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 5\text{ V};$ see <a href="#">Figure 1</a>	[1]	-	120	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ see <a href="#">Figure 4</a>	-	1363	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	357	W	
$T_{stg}$	storage temperature		-55	175	°C	
$T_j$	junction temperature		-55	175	°C	
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	[1]	-	120	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}$	-	1363	A	
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 120\text{ A}; V_{sup} \leq 40\text{ V}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 5\text{ V}; T_{j(init)} = 25\text{ °C};$ unclamped; see <a href="#">Figure 3</a>	[2][3]	-	1008	mJ

[1] Continuous current is limited by package.

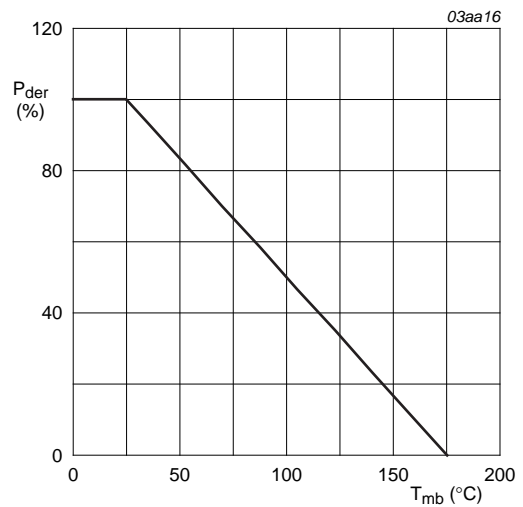
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.



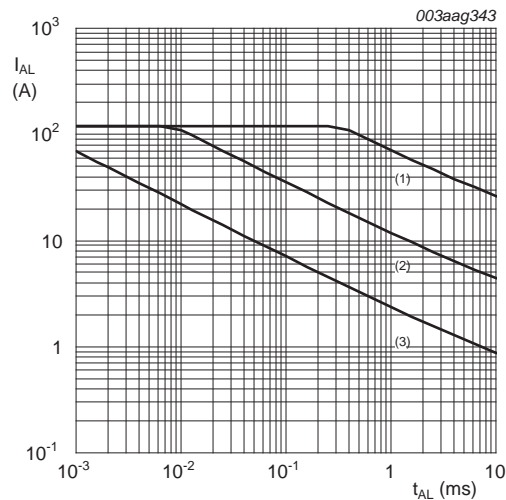
$V_{GS} \geq 5V$   
 (1) Capped at 120 A due to package.

**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



(1)  $T_{j(jst)} = 25^{\circ}C$ ; (2)  $T_{j(jst)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

**Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time**

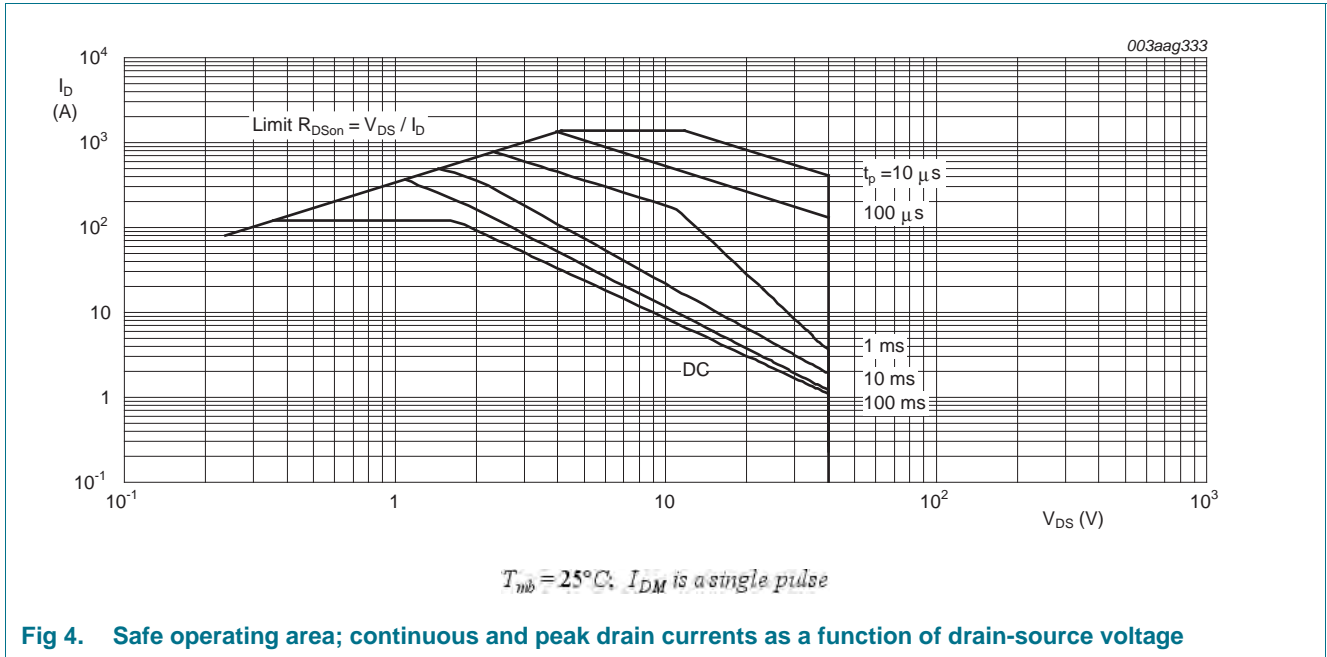


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 5</a>	-	-	0.42	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

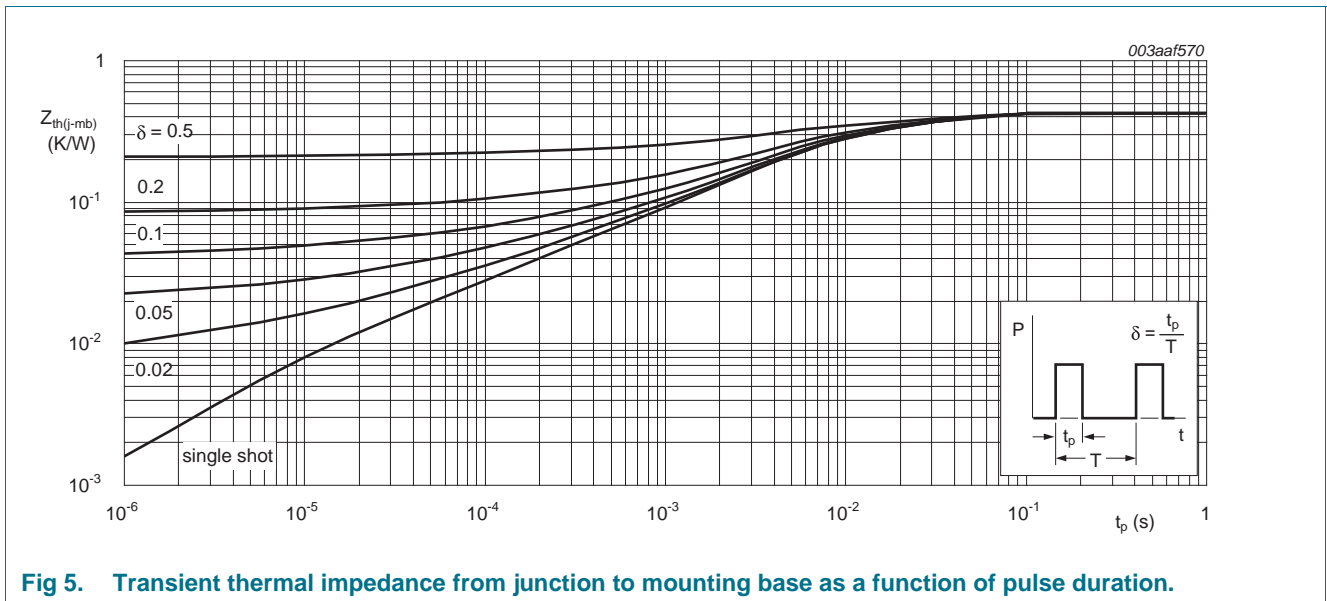
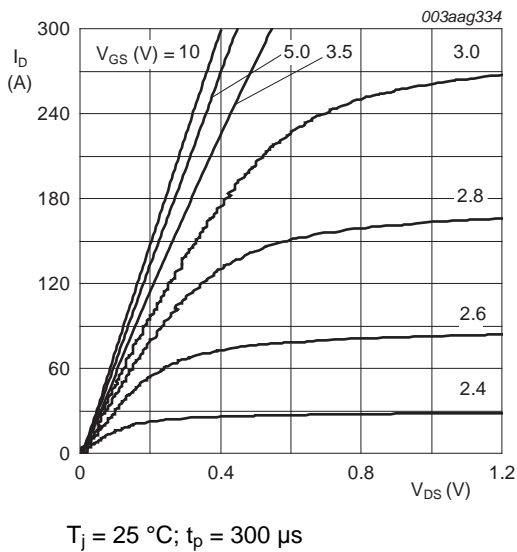


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

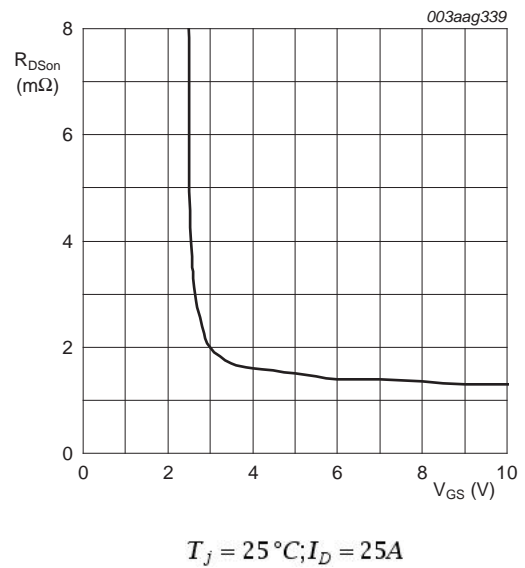
## 7. Characteristics

Table 7. Characteristics

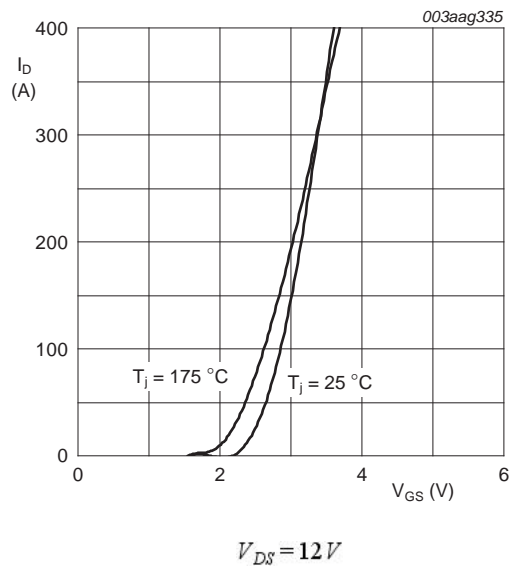
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	40	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a>	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a>	0.5	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.13	1	$\mu\text{A}$
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	-	1.35	1.6	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	-	1.17	1.4	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a> ; see <a href="#">Figure 11</a>	-	-	3.1	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	120	-	nC
$Q_{GS}$	gate-source charge		-	26.9	-	nC
$Q_{GD}$	gate-drain charge		-	40.9	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	12300	16400	pF
$C_{oss}$	output capacitance		-	1530	1840	pF
$C_{rss}$	reverse transfer capacitance		-	740	1020	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \text{ } \Omega$	-	95	-	ns
$t_r$	rise time		-	118	-	ns
$t_{d(off)}$	turn-off delay time		-	195	-	ns
$t_f$	fall time		-	119	-	ns
$L_D$	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
$L_S$	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>	-	0.77	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}$	-	57	-	ns
$Q_r$	recovered charge		-	97	-	nC



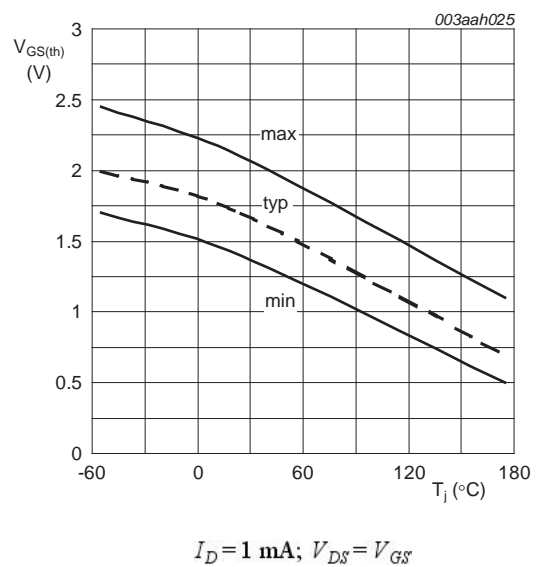
**Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



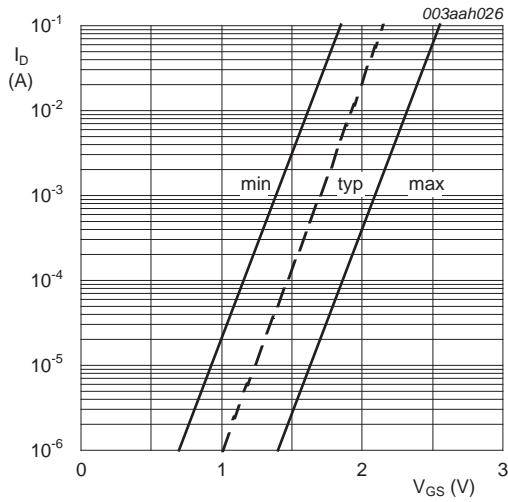
**Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**



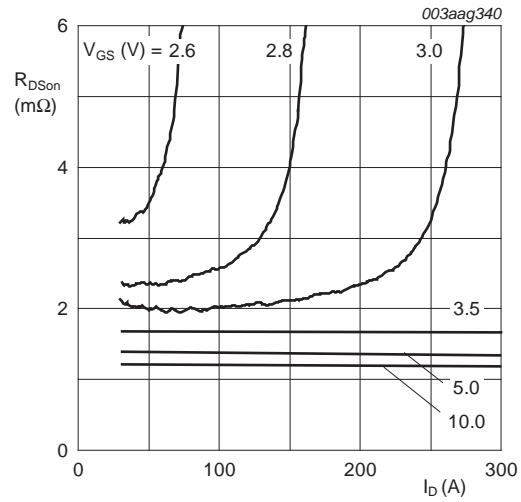
**Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



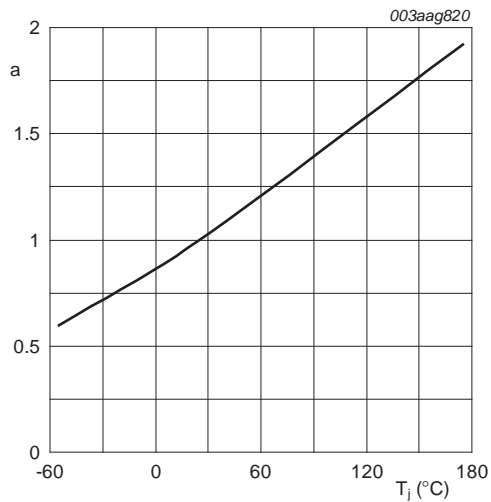
**Fig 9. Gate-source threshold voltage as a function of junction temperature**



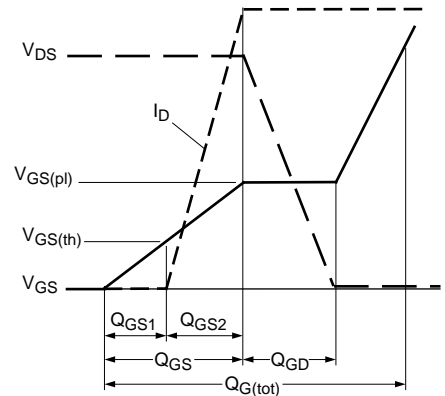
**Fig 10. Sub-threshold drain current as a function of gate-source voltage**



**Fig 11. Drain-source on-state resistance as a function of drain current; typical values**

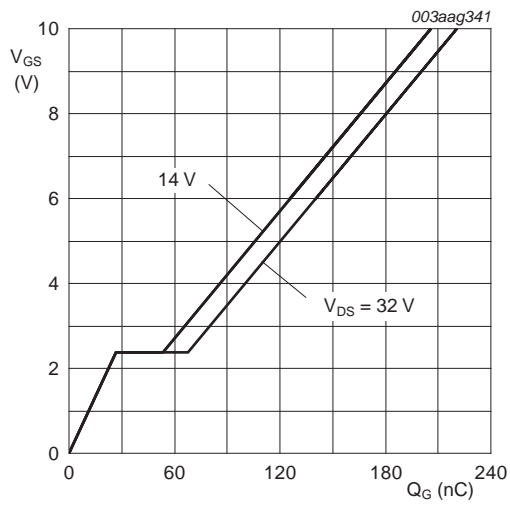


**Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature**



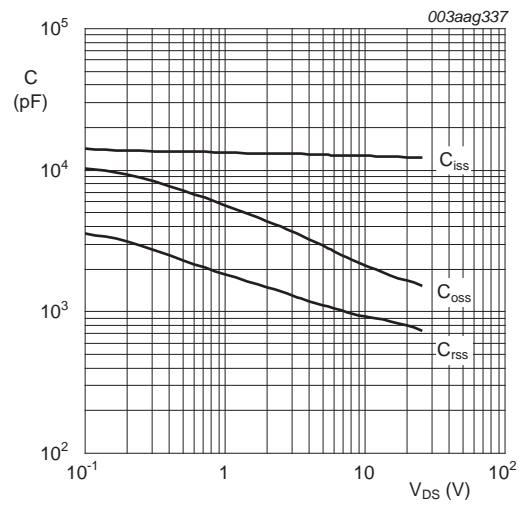
**Fig 13. Gate charge waveform definitions**





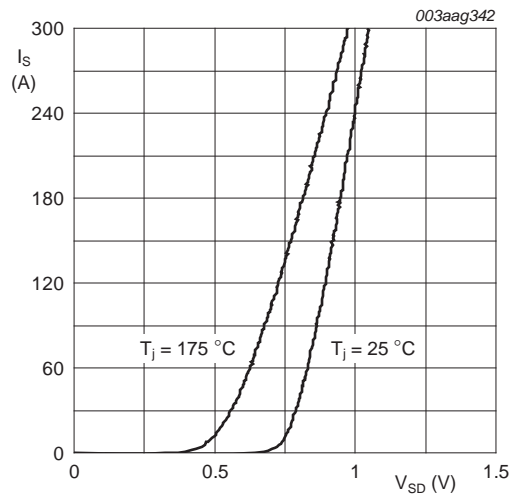
$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

**Fig 14. Gate-source voltage as a function of gate charge; typical values**



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

**Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$V_{GS} = 0\text{ V}$

**Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

**8. Package outline**

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

**SOT404**



**Fig 17. Package outline SOT404 (D2PAK)**

## 9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK961R6-40E v.2	20120516	Product data sheet	-	BUK961R6-40E v.1
Modifications:	<ul style="list-style-type: none"><li>• Status changed from objective to product.</li><li>• Various changes to content.</li></ul>			
BUK961R6-40E v.1	20120404	Objective data sheet	-	-

## 10. Legal information

### 10.1 Data sheet status

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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**12. Contents**

**1 Product profile . . . . .1**

1.1 General description . . . . .1

1.2 Features and benefits . . . . .1

1.3 Applications . . . . .1

1.4 Quick reference data . . . . .1

**2 Pinning information . . . . .2**

**3 Ordering information . . . . .2**

**4 Marking . . . . .2**

**5 Limiting values . . . . .3**

**6 Thermal characteristics . . . . .5**

**7 Characteristics . . . . .6**

**8 Package outline . . . . .10**

**9 Revision history . . . . .11**

**10 Legal information . . . . .12**

10.1 Data sheet status . . . . .12

10.2 Definitions . . . . .12

10.3 Disclaimers . . . . .12

10.4 Trademarks . . . . .13

**11 Contact information . . . . .13**

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